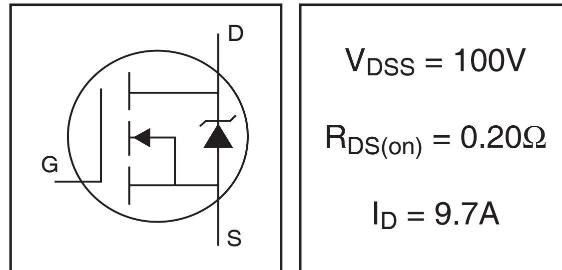
International
IOR Rectifier

PD - 94818

IRF520NPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 100V

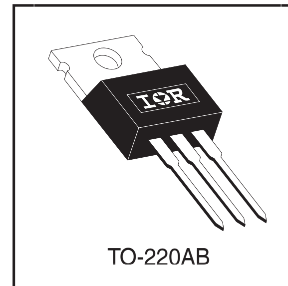
$R_{DS(on)}$ = 0.20Ω

I_D = 9.7A

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

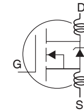
Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	9.7	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	6.8	
I_{DM}	Pulsed Drain Current ①	38	
P_D @T_C = 25°C	Power Dissipation	48	W
	Linear Derating Factor	0.32	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	91	mJ
I_{AR}	Avalanche Current①	5.7	A
E_{AR}	Repetitive Avalanche Energy①	4.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—–	3.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—–	
$R_{\theta JA}$	Junction-to-Ambient	—–	62	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.11	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.20	Ω	V_{GS} = 10V, I_D = 5.7A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	$V_{DS} = V_{GS}$, I_D = 250μA
g_{fs}	Forward Transconductance	2.7	–––	–––	S	V_{DS} = 50V, I_D = 5.7A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	μA	V_{DS} = 100V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 80V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
Q_g	Total Gate Charge	–––	–––	25	nC	I_D = 5.7A
Q_{gs}	Gate-to-Source Charge	–––	–––	4.8		V_{DS} = 80V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	11		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	–––	4.5	–––	ns	V_{DD} = 50V
t_r	Rise Time	–––	23	–––		I_D = 5.7A
$t_{d(off)}$	Turn-Off Delay Time	–––	32	–––		R_G = 22Ω
t_f	Fall Time	–––	23	–––		R_D = 8.6Ω, See Fig. 10 ④
L_D	Internal Drain Inductance	–––	4.5	–––	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	–––	7.5	–––		
C_{iss}	Input Capacitance	–––	330	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	92	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	54	–––		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	9.7	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	38		
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 5.7A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	99	150	ns	T_J = 25°C, I_F = 5.7A
Q_{rr}	Reverse RecoveryCharge	–––	390	580	nC	di/dt = 100A/μs ④

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

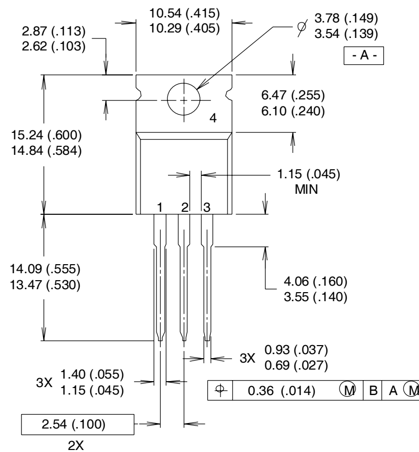
② V_{DD} = 25V, starting T_J = 25°C, L = 4.7mH R_G = 25Ω, I_{AS} = 5.7A. (See Figure 12)

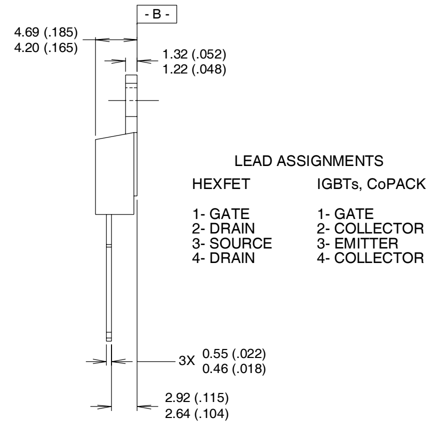
③ $I_{SD} \leq$ 5.7A, di/dt ≤ 240A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)





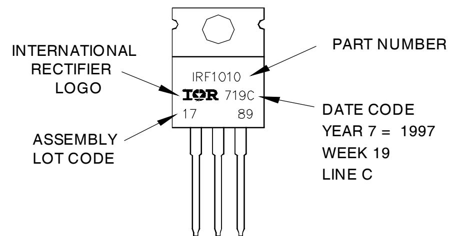
NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.